

# Shunri Oda

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

293  
papers

4,380  
citations

31  
h-index

51  
g-index

357  
ext. papers

4,966  
ext. citations

2.7  
avg, IF

5.27  
L-index

#	Paper	IF	Citations
293	Synthesis and characterization of Ge-core/a-Si-shell nanowires with conformal shell thickness deposited after gold removal for high-mobility p-channel field-effect transistors. <i>Nanoscale Advances</i> , <b>2020</b> , 2, 1465-1472	5.1	1
292	Transfer printing of gate dielectric and carrier doping with poly(vinyl-alcohol) coating to fabricate top-gate molybdenum disulfide field-effect transistors. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, 120903	1.4	1
291	Temperature dependence of hole transport properties through physically defined silicon quantum dots. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 094001	3.4	1
290	Physically defined silicon triple quantum dots charged with few electrons in metal-oxide-semiconductor structures. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 074001	3.4	5
289	Physically defined triple quantum dot systems in silicon on insulator. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 073104	3.4	6
288	Comparison of picosecond electron dynamics in isolated and clustered Si quantum dots deposited on a semiconductor surface. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 053105	3.4	1
287	Transfer printing of Al <sub>2</sub> O <sub>3</sub> gate dielectric for fabrication of top-gate MoS <sub>2</sub> FET. <i>Applied Physics Express</i> , <b>2019</b> , 12, 026501	2.4	2
286	A quantum-dot spin qubit with coherence limited by charge noise and fidelity higher than 99.9. <i>Nature Nanotechnology</i> , <b>2018</b> , 13, 102-106	28.7	340
285	An electronic synaptic device based on HfO <sub>2</sub> /TiO <sub>2</sub> bilayer structure memristor with self-compliance and deep-RESET characteristics. <i>Nanotechnology</i> , <b>2018</b> , 29, 415205	3.4	18
284	Characteristics of multilevel storage and switching dynamics in resistive switching cell of Al <sub>2</sub> O <sub>3</sub> /HfO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> sandwich structure. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 025102	3	14
283	Optimized electrical control of a Si/SiGe spin qubit in the presence of an induced frequency shift. <i>Npj Quantum Information</i> , <b>2018</b> , 4,	8.6	13
282	Control of threshold voltage by gate metal electrode in molybdenum disulfide field-effect transistors. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 133507	3.4	11
281	Charge sensing and spin-related transport property of p-channel silicon quantum dots. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 04CK07	1.4	11
280	Transfer printing of nanostructured membrane with elastomeric stamp and its application to TMDC-based field-effect transistors <b>2017</b> ,		1
279	Observation and coherent control of interface-induced electronic resonances in a field-effect transistor. <i>Nature Materials</i> , <b>2017</b> , 16, 208-213	27	7
278	Use of self-assembled monolayers for selective metal removal and ultrathin gate dielectrics in MoS <sub>2</sub> field-effect transistors. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 04CP10	1.4	2
277	A flexible terahertz scanner for omnidirectional imaging <b>2017</b> ,		1

276	Undoped and catalyst-free germanium nanowires for high-performance p-type enhancement-mode field-effect transistors. <i>Journal of Materials Chemistry C</i> , <b>2016</b> , 4, 5102-5108	7.1	12
275	A flexible and wearable terahertz scanner. <i>Nature Photonics</i> , <b>2016</b> , 10, 809-813	33.9	106
274	Adhesion lithography to fabricate MoS2 FETs with self-assembled monolayer-based gate dielectrics <b>2016</b> ,		3
273	Electron transport in physically-defined double quantum dots on a highly doped silicon-on-insulator substrate. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 113109	3.4	3
272	Utilizing self-assembled-monolayer-based gate dielectrics to fabricate molybdenum disulfide field-effect transistors. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 041605	3.4	24
271	Deionization of Dopants in Silicon Nanofilms Even with Donor Concentration of Greater than $10^{19}$ cm <sup>-3</sup> . <i>Nano Letters</i> , <b>2016</b> , 16, 1143-9	11.5	2
270	Scaling dependence of memory windows and different carrier charging behaviors in Si nanocrystal nonvolatile memory devices. <i>Chinese Physics B</i> , <b>2016</b> , 25, 097304	1.2	
269	Experimental Study on Deformation Potential ( $D_{ac}$ ) in MOSFETs: Demonstration of Increased $D_{ac}$ at MOS Interfaces and Its Impact on Electron Mobility. <i>IEEE Journal of the Electron Devices Society</i> , <b>2016</b> , 4, 278-285	2.3	5
268	Effect of gold migration on the morphology of germanium nanowires grown by a two-step growth method with temperature modulation. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 085002	1.4	
267	A fault-tolerant addressable spin qubit in a natural silicon quantum dot. <i>Science Advances</i> , <b>2016</b> , 2, e1600694	14.5	120
266	Electron transport through a single nanocrystalline silicon quantum dot between nanogap electrodes. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 213102	3.4	1
265	Coupled quantum dots on SOI as highly integrated Si qubits <b>2016</b> ,		3
264	Thickness dependence of terahertz plasmonic antenna <b>2016</b> ,		1
263	Split-joint bullseye structure with aperture optimization for multi-frequency terahertz plasmonic antennas <b>2016</b> ,		1
262	Mechanism of carbon nanotubes terahertz detectors based on photothermoelectric effect <b>2016</b> ,		1
261	Back-action-induced excitation of electrons in a silicon quantum dot with a single-electron transistor charge sensor. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 053119	3.4	10
260	Sn-Guided Defect-Free GeSn Lateral Growth on Si by Molecular Beam Epitaxy. <i>Journal of Physical Chemistry C</i> , <b>2015</b> , 119, 17842-17847	3.8	6
259	Quantum dots in single electron transistors with ultrathin silicon-on-insulator structures. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 013102	3.4	13

258	Lithographically defined few-electron silicon quantum dots based on a silicon-on-insulator substrate. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 083111	3.4	18
257	Ge/Si core/shell nanowires with controlled low temperature grown Si shell thickness. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 1578-1581	1.6	1
256	Proposal for fast-response radial Schottky junction photodetectors based on silicon nanowires. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 034301	1.4	0
255	Formation of three-dimensionally integrated nanocrystalline silicon particles by dip-coating method. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 105001	1.4	0
254	Visualization of Ultrafast Electron Dynamics Using Time-Resolved Photoemission Electron Microscopy. <i>Springer Proceedings in Physics</i> , <b>2015</b> , 337-340	0.2	1
253	Coupled Si Quantum Dots for Spin-Based Qubits <b>2015</b> , 231-253		
252	Charge noise analysis of metal oxide semiconductor dual-gate Si/SiGe quantum point contacts. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 203709	2.5	1
251	In situ monitoring of silicon nanocrystal formation with pulsed SiH <sub>4</sub> supply by optical emission spectroscopy of Ar plasma. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 116102	1.4	4
250	GHz photon-activated hopping between localized states in a silicon quantum dot. <i>New Journal of Physics</i> , <b>2014</b> , 16, 013016	2.9	2
249	Fabrication and characterization of p-channel Si double quantum dots. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 113110	3.4	8
248	Experimental study on SET/RESET conditions for graphene resistive random access memory. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 04EN02	1.4	2
247	Surface passivation of germanium nanowires using Al <sub>2</sub> O <sub>3</sub> and HfO <sub>2</sub> deposited via atomic layer deposition technique. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 06JG04	1.4	8
246	Optimization and Tunnel Junction Parameters Extraction of Electrostatically Defined Silicon Double Quantum Dots Structure. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 081301	1.4	
245	Microscopic study of germanium nanowires grown via gold-catalyzed chemical vapor deposition below the eutectic temperature. <i>Journal of Crystal Growth</i> , <b>2013</b> , 384, 77-81	1.6	3
244	GaAs/AlGaAs field-effect transistor for tunable terahertz detection and spectroscopy with built-in signal modulation. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 122102	3.4	10
243	Dual Function of Single Electron Transistor Coupled with Double Quantum Dot: Gating and Charge Sensing. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 04CJ01	1.4	13
242	Experimental Study of Two-Terminal Resistive Random Access Memory Realized in Mono- and Multilayer Exfoliated Graphene Nanoribbons. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 04CN05	1.4	4
241	Methodology for Evaluating Operation Temperatures of Fin-Type Field-Effect Transistors Connected by Interconnect Wires. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 064203	1.4	9

240	Self-Heating Effects and Analog Performance Optimization of Fin-Type Field-Effect Transistors. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 04CC03	1.4	13
239	Channel Length Scaling and Surface Nitridation of Silicon Nanocrystals for High-Performance Electron Devices. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 04CH08	1.4	0
238	Characterization and suppression of low-frequency noise in Si/SiGe quantum point contacts and quantum dots. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 123113	3.4	21
237	Impact of Deformation Potential Increase at Si/SiO <sub>2</sub> Interfaces on Stress-Induced Electron Mobility Enhancement in Metal Oxide Semiconductor Field-Effect Transistors. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 04CC12	1.4	4
236	Conduction Bottleneck in Silicon Nanochain Single Electron Transistors Operating at Room Temperature. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 025202	1.4	2
235	High ON/OFF ratio and multimode transport in silicon nanochains field effect transistors. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 113108	3.4	5
234	Experimental study of self-heating effect (SHE) in SOI MOSFETs: Accurate understanding of temperatures during AC conductance measurement, proposals of 2 $\pi$ method and modified pulsed IV <b>2012</b> ,		20
233	A Multi-Purpose Electrostatically Defined Silicon Quantum Dot Structure. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 02BJ10	1.4	1
232	Photoluminescence of Nanocrystalline Silicon Quantum Dots with Various Sizes and Various Phosphorus Doping Concentrations Prepared by Very High Frequency Plasma. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 115202	1.4	3
231	Temperature Evolution of Spin-Polarized Electron Tunneling in Silicon Nanowire/Alloy Lateral Spin Valve System. <i>Applied Physics Express</i> , <b>2012</b> , 5, 045001	2.4	5
230	Key capacitive parameters for designing single-electron transistor charge sensors. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 093715	2.5	11
229	Magnetic field dependence of Pauli spin blockade: A window into the sources of spin relaxation in silicon quantum dots. <i>Physical Review B</i> , <b>2012</b> , 86,	3.3	40
228	Localization effects in the tunnel barriers of phosphorus-doped silicon quantum dots. <i>AIP Advances</i> , <b>2012</b> , 2, 022114	1.5	4
227	Conduction Bottleneck in Silicon Nanochain Single Electron Transistors Operating at Room Temperature. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 025202	1.4	6
226	Photoluminescence of Nanocrystalline Silicon Quantum Dots with Various Sizes and Various Phosphorus Doping Concentrations Prepared by Very High Frequency Plasma. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 115202	1.4	8
225	A Multi-Purpose Electrostatically Defined Silicon Quantum Dot Structure. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 02BJ10	1.4	
224	Germanium nanowires with 3-nm-diameter prepared by low temperature vapour-liquid-solid chemical vapour deposition. <i>Journal of Nanoscience and Nanotechnology</i> , <b>2011</b> , 11, 8163-8	1.3	11
223	Experimental evidence of increased deformation potential at MOS interface and its impact on characteristics of ETSOI FETs <b>2011</b> ,		8

222	Temperature insensitive conductance detection with surface-functionalised silicon nanowire sensors. <i>Microelectronic Engineering</i> , <b>2011</b> , 88, 1753-1756	2.5	1
221	Growth of GeBi nanowire heterostructures via chemical vapor deposition. <i>Thin Solid Films</i> , <b>2011</b> , 519, 4174-4176	2.2	7
220	Size Reduction and Phosphorus Doping of Silicon Nanocrystals Prepared by a Very High Frequency Plasma Deposition System. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 025002	1.4	8
219	Study on Device Parameters of Carbon Nanotube Field Electron Transistors to Realize Steep Subthreshold Slope of Less than 60 mV/Decade. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 04DN01	1.4	7
218	Removal of Surface Oxide Layer from Silicon Nanocrystals by Hydrogen Fluoride Vapor Etching. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 115002	1.4	5
217	Experimental Study on Electron Mobility in Accumulation-Mode Silicon-on-Insulator MetalOxideSemiconductor Field-Effect Transistors. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 094101	1.4	5
216	Simulation Study of Charge Modulation in Coupled Quantum Dots in Silicon. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 04DJ05	1.4	2
215	Numerical simulation study of electrostatically defined silicon double quantum dot device. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 054511	2.5	3
214	Tip-enhanced Raman mapping of a single Ge nanowire. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 053112	3.4	30
213	Electron mobility enhancement in nanoscale silicon-on-insulator diffusion layers with high doping concentration of greater than $1 \times 10^{18} \text{ cm}^{-3}$ and silicon-on-insulator thickness of less than 10 nm. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 034502	2.5	8
212	Detection of variable tunneling rates in silicon quantum dots. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 133506	3.4	4
211	Experimental study on subband structures and hole transport in (110) Si p-type metal-oxide-semiconductor field-effect transistors under high magnetic field. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 034505	2.5	3
210	Demonstration of spin valve effects in silicon nanowires. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 07C508	2.5	10
209	Thermal-aware device design of nanoscale bulk/SOI FinFETs: Suppression of operation temperature and its variability <b>2011</b> ,		25
208	Growth of Narrow and Straight Germanium Nanowires by VaporLiquidSolid Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 105002	1.4	3
207	Size Reduction and Phosphorus Doping of Silicon Nanocrystals Prepared by a Very High Frequency Plasma Deposition System. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 025002	1.4	5
206	Growth of Narrow and Straight Germanium Nanowires by VaporLiquidSolid Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 105002	1.4	10
205	Removal of Surface Oxide Layer from Silicon Nanocrystals by Hydrogen Fluoride Vapor Etching. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 115002	1.4	6

204	Simulation Study of Charge Modulation in Coupled Quantum Dots in Silicon. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 04DJ05	1.4	
203	Design of New Logic Architectures Utilizing Optimized Suspended-Gate Single-Electron Transistors. <i>IEEE Nanotechnology Magazine</i> , <b>2010</b> , 9, 504-512	2.6	1
202	Current fluctuations in three-dimensionally stacked Si nanocrystals thin films. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 092112	3.4	6
201	Vertical-coupled SiGe double quantum dots. <i>Electronics Letters</i> , <b>2010</b> , 46, 940	1.1	1
200	Experimental Observation of Enhanced Electron-Phonon Interaction in Suspended Si Double Quantum Dots. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 045203	1.4	9
199	Suspended Quantum Dot Fabrication on a Heavily Doped Silicon Nanowire by Suppressing Unintentional Quantum Dot Formation. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 044001	1.4	3
198	Scaling Analysis of Nanoelectromechanical Memory Devices. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 044304	1.4	8
197	Silicon Nanocrystal Flash Memory <b>2010</b> , 395-444		2
196	Fabrication of Nanosilicon Ink and Two-Dimensional Array of Nanocrystalline Silicon Quantum Dots. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 125002	1.4	3
195	Anomalous electron mobility in extremely-thin SOI (ETSOI) diffusion layers with SOI thickness of less than 10 nm and high doping concentration of greater than $1 \times 10^{18} \text{cm}^{-3}$ <b>2010</b> ,		1
194	Position-Controllable Ge Nanowires Growth on Patterned Au Catalyst Substrate. <i>Applied Physics Express</i> , <b>2009</b> , 2, 015004	2.4	11
193	Control of Inter-Dot Electrostatic Coupling by a Side Gate in a Silicon Double Quantum Dot Operating at 4.5 K. <i>Applied Physics Express</i> , <b>2009</b> , 2, 095002	2.4	19
192	Single Hole Charging at Room Temperature of Ge Quantum Dots Grown on Si(001) by Molecular Beam Epitaxy. <i>Nanoscience and Nanotechnology Letters</i> , <b>2009</b> , 1, 82-86	0.8	2
191	Carrier transport by field enhanced thermal detrapping in Si nanocrystals thin films. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 124518	2.5	11
190	Electromechanical Simulation of Switching Characteristics for Nanoelectromechanical Memory. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 114502	1.4	5
189	Electron transport in surface oxidized Si nanocrystal ensembles with thin film transistor structure. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 044511	2.5	11
188	Spontaneous emission control of silicon nanocrystals by silicon three-dimensional photonic crystal structure fabricated by self-aligned two-directional electrochemical etching method. <i>Materials Chemistry and Physics</i> , <b>2009</b> , 116, 107-111	4.4	4
187	Electron transport through silicon serial triple quantum dots. <i>Solid-State Electronics</i> , <b>2009</b> , 53, 779-785	1.7	11

186	Design Optimization of NEMS Switches for Suspended-Gate Single-Electron Transistor Applications. <i>IEEE Nanotechnology Magazine</i> , <b>2009</b> , 8, 174-184	2.6	11
185	Electron Transport in Nanocrystalline Silicon. <i>Nanostructure Science and Technology</i> , <b>2009</b> , 197-221	0.9	2
184	Strongly coupled multiple-dot characteristics in dual recess structured silicon channel. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 043719	2.5	1
183	Impact of Key Circuit Parameters on Signal-to-Noise Ratio Characteristics for the Radio Frequency Single-Electron Transistors. <i>IEEE Nanotechnology Magazine</i> , <b>2008</b> , 7, 266-272	2.6	6
182	Enhanced tunnel conductance due to QCA cotunneling processes observed for silicon serial triple quantum dots <b>2008</b> ,		1
181	Transient response analysis of programming/readout characteristics for NEMS memory <b>2008</b> ,		2
180	Study of Single-Charge Polarization on a Pair of Charge Qubits Integrated Onto a Silicon Double Single-Electron Transistor Readout. <i>IEEE Nanotechnology Magazine</i> , <b>2008</b> , 7, 617-623	2.6	6
179	Controlled Ge nanowires growth on patterned Au catalyst substrate <b>2008</b> ,		1
178	Formation Mechanism of 100-nm-Scale Periodic Structures in Silicon Using Magnetic-Field-Assisted Anodization. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 7398-7402	1.4	16
177	Vapor-Liquid-Solid Growth of Small- and Uniform-Diameter Silicon Nanowires at Low Temperature from Si <sub>2</sub> H <sub>6</sub> . <i>Applied Physics Express</i> , <b>2008</b> , 1, 014003	2.4	16
176	Theoretical Study of Nonequilibrium Electron Transport and Charge Distribution in a Three-Site Quantum Wire. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 371-382	1.4	3
175	Synthesis of Assembled Nanocrystalline Si Dots Film by the Langmuir-Blodgett Technique. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 3731-3734	1.4	6
174	Control of Electrostatic Coupling Observed for Silicon Double Quantum Dot Structures. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 4820-4826	1.4	17
173	Size-Dependent Structural Characterization of Silicon Nanowires. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 5053-5056	1.4	6
172	Visible Electroluminescence from Spherical-Shaped Silicon Nanocrystals. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 8137-8140	1.4	22
171	Silicon quantum dot devices <b>2008</b> ,		1
170	Voltage-limitation-free analytical single-electron transistor model incorporating the effects of spin-degenerate discrete energy states. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 054508	2.5	8
169	Room temperature single electron charging in single silicon nanochains. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 053705	2.5	26



168	Stochastic Coulomb blockade in coupled asymmetric silicon dots formed by pattern-dependent oxidation. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 092110	3.4	7
167	Impact of channel constrictions on the formation of multiple tunnel junctions in heavily doped silicon single electron transistors. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 112107	3.4	7
166	Field-dependant hopping conduction in silicon nanocrystal films. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 123710	2.5	9
165	Silicon-on-insulator-based radio frequency single-electron transistors operating at temperatures above 4.2 K. <i>Nano Letters</i> , <b>2008</b> , 8, 4648-52	11.5	16
164	Nonequilibrium transport properties for a three-site quantum wire model. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 56-60		1
163	Single-electron tunnelling via quantum dot cavities built on a silicon suspension nanobridge. <i>Microelectronic Engineering</i> , <b>2008</b> , 85, 1410-1412	2.5	8
162	Influence of the crystal orientation of substrate on low temperature synthesis of silicon nanowires from Si <sub>2</sub> H <sub>6</sub> . <i>Thin Solid Films</i> , <b>2008</b> , 517, 317-319	2.2	10
161	Bottom-up approach to silicon nanoelectronics. <i>Microelectronics Journal</i> , <b>2008</b> , 39, 171-176	1.8	10
160	Influence of nanocrystal size on the transport properties of Si nanocrystals. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 024518	2.5	25
159	Charge storage and electron/light emission properties of silicon nanocrystals. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2007</b> , 38, 59-63	3	10
158	Three-Dimensional Numerical Analysis of Switching Properties of High-Speed and Nonvolatile Nanoelectromechanical Memory. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 1132-1139	2.9	13
157	New Design Concept and Fabrication Process for Three-Dimensional Silicon Photonic Crystal Structures. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 633-637	1.4	8
156	Integration of Tunnel-Coupled Double Nanocrystalline Silicon Quantum Dots with a Multiple-Gate Single-Electron Transistor. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 4386-4389	1.4	17
155	3-D Design and Analysis of Functional NEMS-gate MOSFETs and SETs. <i>IEEE Nanotechnology Magazine</i> , <b>2007</b> , 6, 218-224	2.6	18
154	Observation of interdot coupling phenomena in nanocrystalline silicon point-contact structures. <i>Current Applied Physics</i> , <b>2006</b> , 6, 536-540	2.6	1
153	Observation and Analysis of Tunneling Properties of Single Spherical Nanocrystalline Silicon Quantum Dot. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, 3638-3641	1.4	6
152	Hopping conduction in size-controlled Si nanocrystals. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 014303	2.5	42
151	Broadband variable chromatic dispersion in photonic-band electro-optic waveguide <b>2006</b> ,		1

150	Nanoelectromechanical nonvolatile memory device incorporating nanocrystalline Si dots. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 094306	2.5	29
149	High-density assembly of nanocrystalline silicon quantum dots. <i>Current Applied Physics</i> , <b>2006</b> , 6, 344-347	2.6	14
148	Inter-grain coupling effects on Coulomb oscillations in dual-gated nanocrystalline silicon point-contact transistors. <i>Thin Solid Films</i> , <b>2005</b> , 487, 255-259	2.2	
147	Atomic Force Microscope Current-Imaging Study for Current Density through Nanocrystalline Silicon Dots Embedded in SiO <sub>2</sub> . <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L88-L91	1.4	5
146	Charge storage in nitrided nanocrystalline silicon dots. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 173107	3.4	32
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2	ZnS blue-light-emitting diodes with an external quantum efficiency of 51.0%. <i>Applied Physics Letters</i> , <b>1975</b> , 27, 697-699	3.4	71
1	Observation of Quantum Level Spectrum for Silicon Double Single-Electron Transistors. <i>Applied Physics Express</i> , 1, 051401	2.4	1